

JAW EC-400															HF e.r. wafer		LPD (light point defects)		Additional Notes						Brian Lingg, PM
Date	User	Film	Recipe	Substrate T	Thickness	Dep.time	Index @ 632.8nm	Index @ 1550nm	Dep.rate	Stress	(MPa)	(nm/min)	before dep.	after dep.	AVG dep.rate	AVG+10%	AVG-10%	AVG index@	AVG+1%	AVG-1%	AVG.Stress	Avg+20%	Avg-20%	Additional Notes	
1/1/2012	User	SiO2	SiO2_10	250° C																					
01/06/14	Biljana	SiO2	SiO2_10	250	1013.74	176.6	1.463	1.459	34.44	-401.73		284	1059	35.60	39.16	32.04	1.458	1.473	1.444	-391.17	-469.40	-312.93		Deposition done on 4" Si wafer	update this (logbook)
01/23/14	Biljana	SiO2	SiO2_10	250	1068.74	176.6	1.456	1.445	36.34	-375.92	604.23	150	200	35.60	39.16	32.04	1.458	1.473	1.444	-391.17	-469.40	-312.93		Nice film, not many particles	1/23/14
02/03/14	Biljana	SiO2	SiO2_10	250	1047.82	176.6	1.456	1.451	35.60	-346.54	604.71	304	451	35.60	39.16	32.04	1.458	1.473	1.444	-391.17	-469.40	-312.93		Film is much darker in the center	
02/18/14	Biljana	SiO2	SiO2_10	250	1031.00	176.6	1.454	1.444	35.03	-397.81	545.75	48	274	35.60	39.16	32.04	1.458	1.473	1.444	-391.17	-469.40	-312.93		Film darker in the center	2/14/14 Silane change
03/14/14	Biljana	SiO2	SiO2_10	250	1053.21	176.6	1.455	1.444	35.78	-364.72	600.97	112	222	35.60	39.16	32.04	1.458	1.473	1.444	-391.17	-469.40	-312.93		Film darker in the center	
04/08/14	Biljana	SiO2	SiO2_10	250	1070.80	176.6	1.465	1.454	36.38	-460.47	578.93			35.60	39.16	32.04	1.458	1.473	1.444	-391.17	-469.40	-312.93		Film darker in the center	

Avg.Thickness	1047.72
Avg Index	1.458
Index+1%	1.473
Index-1%	1.444
Avg Dep.Rate	35.60
Avg +10%	39.16
Avg -10%	32.04
Avg.Stress	-391.17
Avg +20%	-469.40
Avg -20%	-312.93
Avg. HF e.r.	586.93

